

Inventor: Sujit Sharan et al.  
Title: Methods of Forming Silicon Dioxide Layers, and Methods of Forming Trench Isolation Regions  
Assignee: Micron Technology, Inc.  
Docket No.: MI22-1421

**INFORMATION DISCLOSURE STATEMENT**  
**PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98**

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

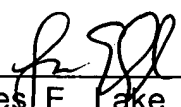
The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a continuation application of co-pending application Serial No. 09/497,080, filed February 2, 2000. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. § 1.98(d) and MPEP § 609(2).

Citation of these references is respectfully requested.

Respectfully submitted,

Dated: 30 Mar 2004

Attorney: \_\_\_\_\_

  
James E. Lake  
Reg. No. 44,854

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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1421		PRIORITY SERIAL NO. 09/497,080	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT    Sujit Sharan et al.			
				PRIORITY FILING DATE February 2, 2000		PRIORITY GROUP 2825	
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	4,839,306	6/1989	Wakamtsu			
	AB	6,030,881	2/2000	Papasoulitis et al			
	AC	5,872,058	2/1999	Van Cleemput +			
	AD	5,614,055	3/1997	Fairbairn et al			
	AE	5,270,264	12/1993	Andideh et al			
	AF	6,015,759	1/2000	Khan et al			
	AG	5,966,616	10/1999	Woerlee			
	AH	5,968,610	10/1999	Liu et al			
	AI	5,679,606	10/1997	Wang et al			
	AJ	6,077,786	5/1997	Chakravarti et al			
	AK	5,731,241	5/1997	Jang et al			
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes    - No
	AL	WO 97/24761	07/97	PCT			
	AM	EP 0 843 348	11/97	Europe			
	AN	8-8232 and abstract	01/96	Japan			
	AO						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AP		Gross, M., "Silicon Dioxide Trench Filling Process in a Radio-Frequency Hollow Cathode Reactor", J. Vac. Sci. Technol. B11(2), Mar./Apr. 1993, No. 2, pp. 242-248.				
	AQ		Lee et al, "A low Redeposition Rate High Density plasma CVD process for high aspect ratio 175 nm Tehcnology and beyond, IITC 99, pgs 152-154 0-7803-5174-6/99 IEEE				
	AR		Jung et al "Enhancing uniformity of borderless VIA resistance by HDP oxide technology" ST-P06 0-7803-5727-2/99 Pgs. 452-455				
EXAMINER				DATE CONSIDERED			
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant</p>							

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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT    Sujit Sharan et al.	
				PRIORITY FILING DATE February 2, 2000	PRIORITY GROUP 2825

U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA	6,174,785	Parekh et al				
	AB	6,165,854	Wu				
	AC	5,447,884	Fahey et al				
	AD	5,726,090	Jang et al				
	AE	5,660,895	Lee et al				
	AF	6,194,038	Rossman				
	AG	6,217,721	Xu et al				
	AH	6,013,584	M'Saad				
	AI	6,153,509	Wantanbe				
	AJ	5,531,834	Ishizuka et al				
	AK	5,726,097	Yanagida				

FOREIGN PATENT DOCUMENTS							
Document Number	Date	Country	Class	Subclass	Translation		
					Yes	No	
AL	07-76777	Japan					
AM	11-154673	Japan					
AN							
AO							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
	AP		
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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1421	PRIORITY SERIAL NO. 09/497,080			
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT    Sujit Sharan et al.				
				PRIORITY FILING DATE February 2, 2000	PRIORITY GROUP 2825			
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA	6,114,216	11/1996	Yieh et al				
	AB	6,255,211	10/1999	Olsen et al				
	AC	5,180,490	1/2001	Vassiliev et al				
	AD	6,136,685	10/2000	Narwankar et al				
	AE	6,140,208	10/2000	Agahi et al				
	AF	5,763,315	06/1998	Benedict et al				
	AG	6,444,037	09/2002	Frankel et al				
	AH	6,340,435	01/2002	Bjorkman et al				
	AI	6,103,601	08/2000	Lee et al				
	AJ	5,976,993	11/1999	Ravi et al				
	AK	6,346,302	2/2002	Kishimoto				
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	AN							
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